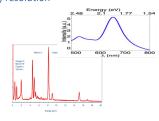


Charged Particles (e , i^+) vs Photons (λ , x)

- Charged Particles are good for:
 - High spatial resolution (< 1 nm routine)
 - Probing /visualizing structure
 - Various forms of Microanalysis (in-elastic scattering)
 - Coupling to plasmons (loss function $Im\{1/\epsilon\}$)



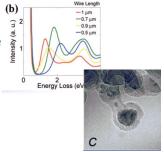
- Photons are good for:
 - In-situ & Atmospheric+ Operation / In-Vivo Studies
 - Various spectroscopies at high spectral (energy) resolution
 - Depending on technique 1 eV -> 1 μeV
 - Microanalysis (X-ray/Optical Spectroscopy)
 - Thick/Bulk specimens (XRD/Synchrotrons)
 - Coupling to electronic excitations/excitons
 - Ultrafast (ps-fs) time resolution
 - **-** \$\$

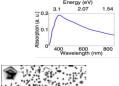


2

Charged Particles (e , i +) vs Photons (λ , x)

- Charged Particles are less desireable because
 - The sample is ubiquitously damaged
 - Time resolution is challenging
 - Usually in Vacuum
 - In-situ possible but more difficult
 - \$\$
- Photons are less capable at:
 - Very high spatial resolution
 - $\sim \lambda/2$ far-field, 30-200 nm in near field
 - Non-transparent/thick specimens (visible light)
 - Coupling to dark modes forbidden excitons, plasmon polaritons





Δ

X-Ray Microscopy - Capabilities

- Large penetration: 10 μm mm (W, Si, 20 keV)
 - ⇒ Study of buried layers and complex devices w/o thinning.
- Use of external fields (magnetic, electric).
- No charging effects.
- Good spatial resolution (but far from fundamental limits)
 - Soft X-ray Microscopy:

 δ ~ 15 nm

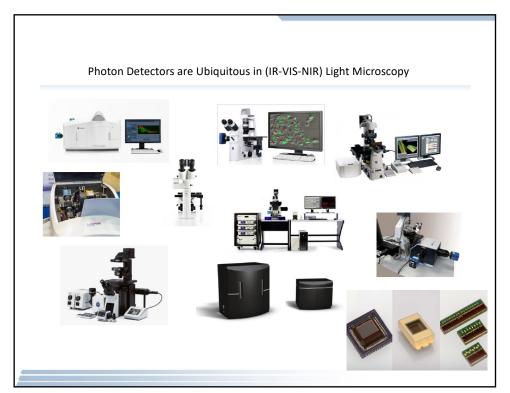
• Future x-ray optics:

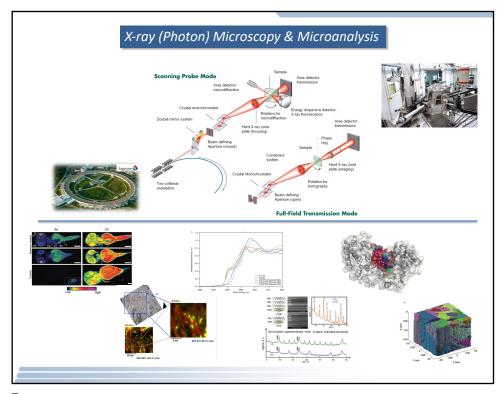
 δ < 10 nm

- Contrast Mechanisms:
 - X-ray fluorescence: atto-g sensitivity (30 nm), quantitative
 - Diffraction: sensitivity to crystallographic phase, strain
 - Transmission imaging in phase/absorption contrast
- Good working distance (>> mm), depth of focus (> um) (E = 10 keV, $dr_N = 10 \text{ nm}$)

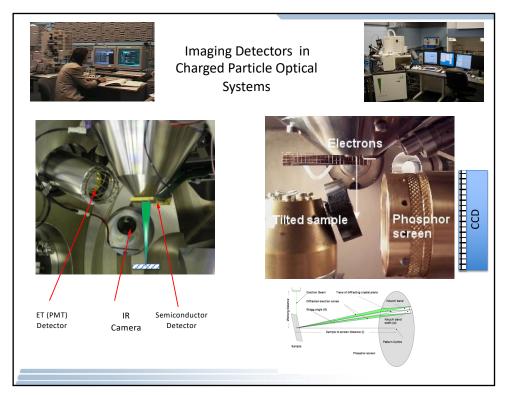
Maser, ICXOM 2013

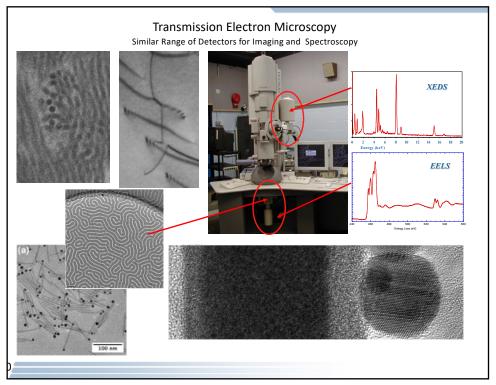
5

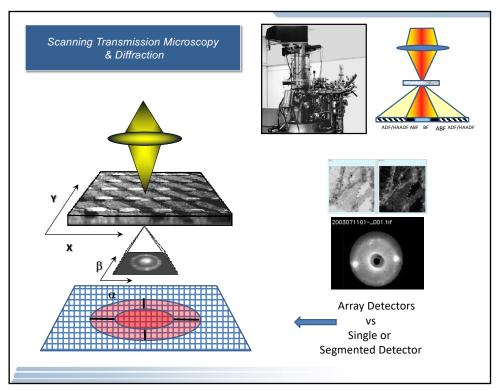


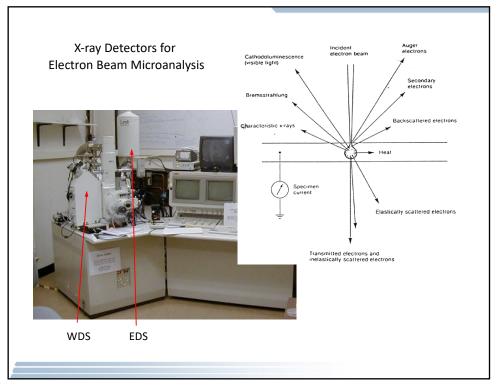


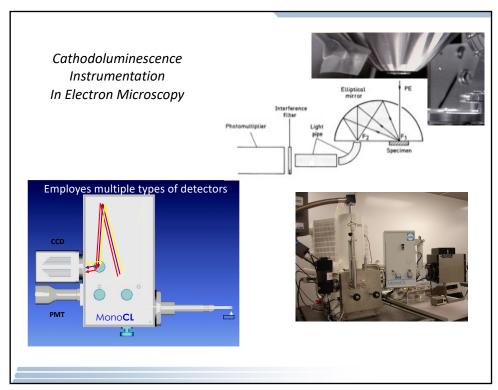
Hard X-ray Microscopy Capabilities at ANL/APS Current high-resolution capabilities at APS: CNM/APS Hard X-ray Nanoprobe, sector 26 • 40 nm resolution in x-ray fluorescence, 30 nm resolution in transmission · Diffraction, fluorescence, tomography APS Bio Nanoprobe, sector 21 • 30 nm resolution, x-ray fluorescence C. Murray et al. Journ. Appl. Cryogenic operation, cryogenic specimen transfer Phys. 109, 083543 (2011) Transmission X-ray microscope, sector 32 • 30 nm resolution, transmission tomography • In-situ capabilities In-Situ Nanoprobe Beamline (APS Upgrade) Science Thrust: Photovoltaics, Energy Storage, Nanoscale Electronics, Catalysis 20 nm – 50 nm resolution at 10 – 1000x increased flux In-situ fluorescence spectroscopy, tomography Sensitivity to << 100 atoms in buried structures/interfaces Coherent scattering to map defects at < 10 nm. H Xiong et al., J. Phys. Chem. Lett., 2, 2560-2565 (2011) Maser, ICXOM 2013

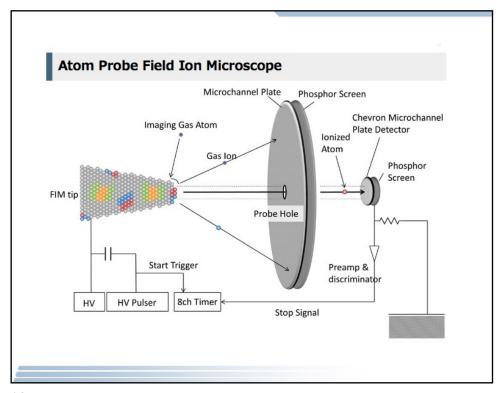












Detectors

- Vacuum/Ionization devices: Traditional Technology
 - o Photomultiplier Tubes (PMT)
 - o MicroChannel Plate (MCP)
 - o Hybrid Detectors (HD)
 - o Ion Detectors (ID)
 - o Ionization Chambers (IC)
- Solid State devices: Rapidly Evolving Technology
 - o PhotoDiodes (PD)
 - o Silicon Photomultipliers (SiPM)
 - o Avalanche Photo Diode : APD
 - o Geiger Mode APD: Arrays of SPAD: SiPM / MPPC ...
 - o Imaging devices: CCD and sCMOS, EMCCD
 - o X-ray Detectors: Si(Li), SDD....

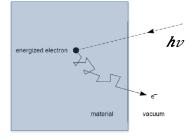


15

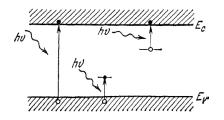
The photoelectric effect is generally responsible for the Signal ($\hbar v$) detection by creating a measurable signal

Two types:

- 1. External: the Photo-electron is emitted into the vacuum from a photocathode material.
- 2. Internal: the Photo-electron is excited and occupies the conduction band of the semiconductor material, the photoconductive effect



External
PhotoElectron
escapes the material

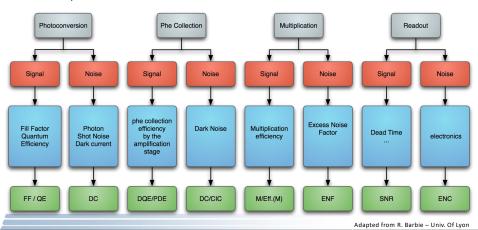


Internal
PhotoElectron
in the Conduction band

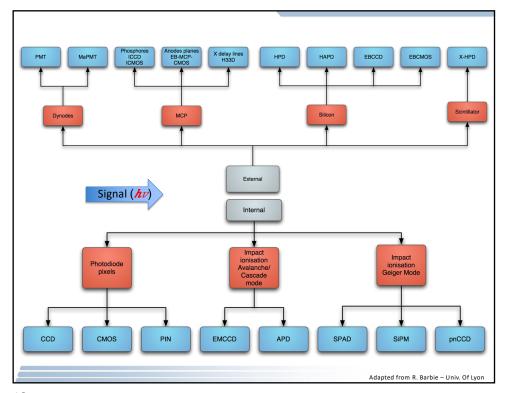
The 4 generic steps in the Detection process:

- 1. The initial charge carrier (pe, e/h) is produced by the Signal $(\hbar \nu)$
- 2. The primary charge carrier is collected
- 3. The primary charge carrier is multiplied/amplified or not (CMOS/CCD/PD/SDD/Si-Li)
- 4. The secondary (or primary) charges are collected and read out

The measurement process is modified by noise sources and by signal collection inefficiency at each step:



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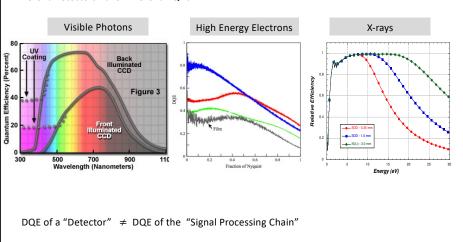




Detector Quantum Efficiency (DQE): probability that a single event triggers a detectable output signal

$$DQE = \frac{Output \, Signal}{Input \, Signal} \leq 1$$

Different Detectors have Different DQE's



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The choice of Detector should be made in light of the question:

What do you want to measure?

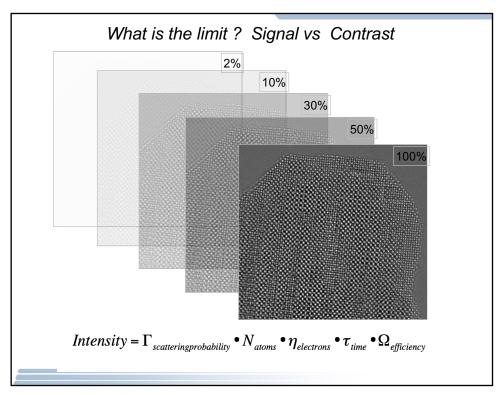
Choose your hierarchy of priorities:

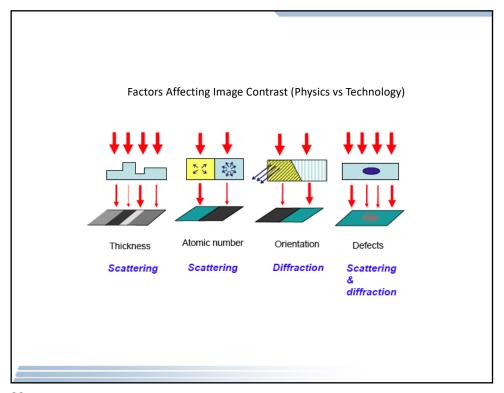
- Counting? Linearity? Single Photon sensitivity?
- Localize ? Imaging ? Large Field of View ? Detection surface ?
- dynamic range ?
- temporal resolution? dead time ?
- ..

Different detectors exist and the "best" for the application is not always obvious.

The detection technologies are evolving rapidly.

Our speakers will be addressing the range typical to Microscopy/Microanalysis





Contrast Mechanisms

Elastic

Amplitude (Mass/Thickness) Contrast Varying mass of the specimen attenuates the beam

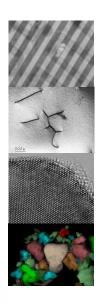
Diffraction Contrast

Scattered beams are removed or signal from scattered events is used

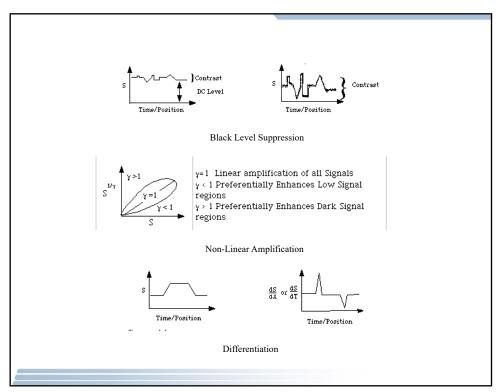
Phase (Interference) Contrast Scattered beams constructively or destructively intereact with each other

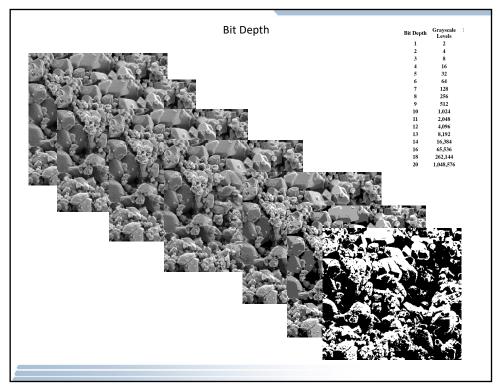
Inelastic

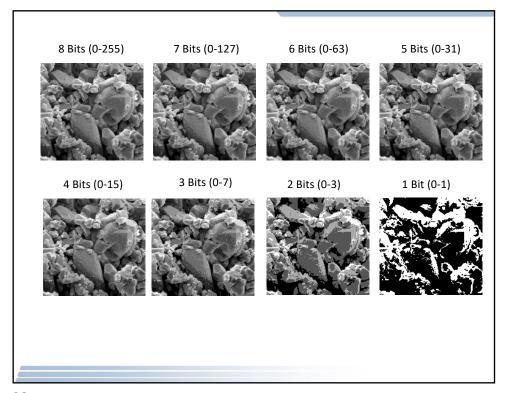
Signal derived from probe changing energy/momentum in the specimen

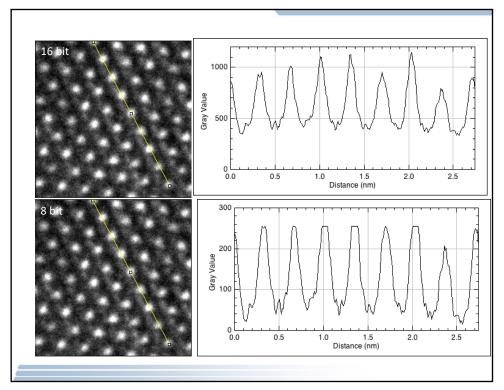


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Signal-to-noise Ratio 2 frames 8 frames 32 frames Collect data with adequate signal-to-noise ratio through image frame summation and/or by proper dwell time (pixel or frame time) setting.

